

Product data sheet

1. General description

Dual ultrafast power diode in a SOT404 (D2PAK) surface-mountable plastic package.

2. Features and benefits

- High reverse voltage surge capability
- High thermal cycling performance
- Low thermal resistance
- Very low on-state loss
- · Soft recovery characteristic minimizes power consuming oscillations
- Surface-mountable package

3. Applications

• Output rectifiers in high-frequency switched-mode power supplies

4. Quick reference data

| Symbol | Parameter | Conditions | v | alues | | Unit |
|------------------|------------------------------------|---|---|-------|------|------|
| | | Conditione | | | | |
| Absolute | maximum rating | | | | | |
| V_{RRM} | repetitive peak reverse voltage | | | 200 | | V |
| $I_{O(AV)}$ | average output current | δ = 0.5; square-wave pulse; T _{mb} ≤ 115 °C; both diodes conducting; <u>Fig. 1</u> ; <u>Fig. 2</u> | | 20 | | A |
| I _{RRM} | repetitive peak reverse current | δ = 0.001; t _p = 2 μs; | | 0.2 | | A |
| V_{ESD} | electrostatic discharge voltage | HBM; C = 250 pF; R = 1.5 k Ω ; all pins | 8 | | kV | |
| Static ch | aracteristics | | | | · | |
| V _F | forward voltage | I _F = 8 A; T _j = 150 °C; <u>Fig. 4</u> | - | 0.72 | 0.85 | V |
| | | I _F = 20 A; T _j = 25 °C | - | 1 | 1.15 | V |
| Dynamic | characteristics | | | | · | |
| t _{rr} | reverse recovery time | $I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 100 \text{ A/}\mu\text{s};$ $T_i = 25 \text{ °C}; \text{ ramp recovery}; Fig. 5$ | - | 20 | 25 | ns |

5. Pinning information

| Table 2. F | Pinning infor | mation | | |
|------------|---------------|------------------------|---------------------|----------------|
| Pin | Symbol | Description | Simplified outline | Graphic symbol |
| 1 | A1 | anode 1 | | |
| 2 | К | cathode [1] | | |
| 3 | A2 | anode 2 | | |
| mb | K | mounting base; cathode | 1 TO-263 (D2PAK) | K sym125 |

[1] it is not possible to make a connection to pin 2 of the SOT404 package

6. Ordering information

| Table 3. Ordering information | | | | | | |
|-------------------------------|---------|--|---------|--|--|--|
| Type number | Package | | | | | |
| | Name | Description | Version | | | |
| BYV32EB-200 | D2PAK | plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped) | SOT404 | | | |

7. Marking

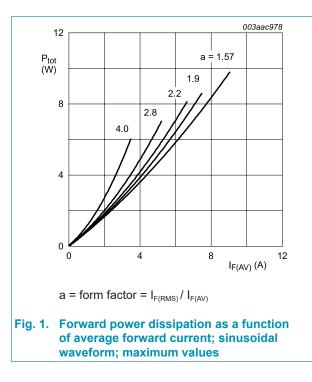
| Table 4. Marking codes | | | | | |
|------------------------|---------------|--|--|--|--|
| Type number | Marking codes | | | | |
| BYV32EB-200 | BYV32EB-200 | | | | |

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | Values | Unit |
|--------------------|--|--|------------|------|
| V _{RRM} | repetitive peak reverse voltage | | 200 | V |
| V_{RWM} | crest working reverse voltage | | 200 | V |
| V _R | reverse voltage | DC | 200 | V |
| I _{O(AV)} | average output current | δ = 0.5; square-wave pulse; T _{mb} ≤ 115 °C; both diodes conducting; <u>Fig 1</u> ; <u>Fig 2</u> | 20 | A |
| I _{FRM} | repetitive peak forward current | δ = 0.5; t _p = 25 μs; T _{mb} ≤ 115 °C; per diode | 20 | A |
| I _{FSM} | non-repetitive peak forward current | t_p = 10 ms; sine-wave pulse; $T_{j(init)}$ = 25 °C; per diode | 125 | A |
| | | t_p = 8.3 ms; sine-wave pulse; $T_{j(init)}$ = 25 °C; per diode | 137 | A |
| I _{RRM} | repetitive peak reverse current | δ = 0.001; t _p = 2 µs; per diode | 0.2 | A |
| I _{RSM} | non-repetitive peak reverse current | t _p = 100 μs; per diode | 0.2 | A |
| T _{stg} | storage temperature | | -40 to 150 | °C |
| Tj | junction temperature | | 150 | °C |
| V_{ESD} | electrostatic discharge voltage | HBM; all pins; C = 250 pF; R = 1.5 k Ω | 8 | kV |



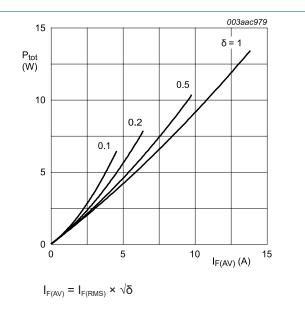
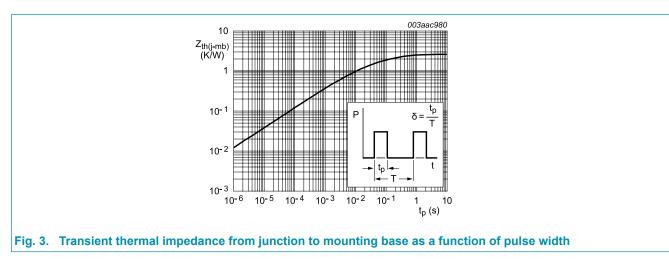


Fig. 2. Forward power dissipation as a function of average forward current; square waveform; maximum values

9. Thermal characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|----------------------|---|---|-----|-----|-----|------|
| $R_{th(j-mb)}$ | thermal resistance from junction to | with heatsink compound; both diodes conducting | - | - | 1.6 | K/W |
| | mounting base | with heatsink compound; per diode; Fig 3 | - | - | 2.4 | K/W |
| $R_{\text{th(j-a)}}$ | thermal resistance from junction to ambient | | - | 60 | - | K/W |



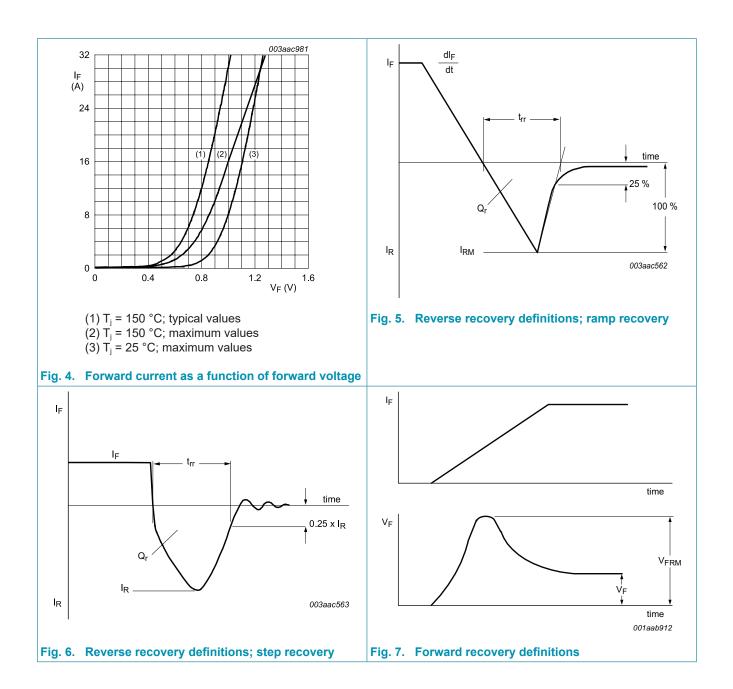
Dual ultrafast power diode

10. Characteristics

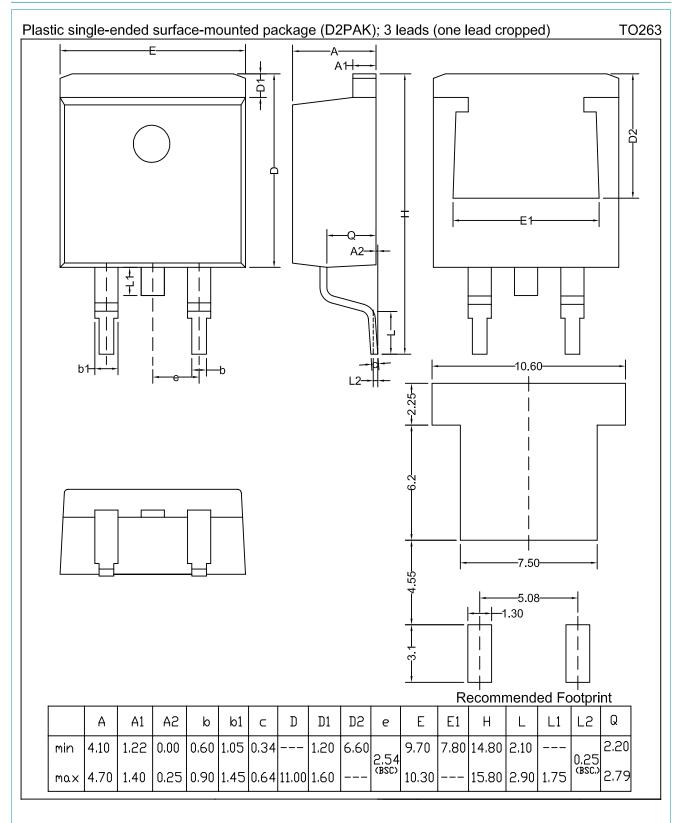
| Symbol | Parameter | Conditions | N | lin | Тур | Max | Unit |
|-----------------|--------------------------|---|---|-----|------|------|------|
| Static cha | racteristics | | | , | | | |
| V_{F} | forward voltage | I _F = 8 A; T _j = 150 °C; <u>Fig. 4</u> | - | | 0.72 | 0.85 | V |
| | | I _F = 20 A; T _j = 25 °C | - | | 1 | 1.15 | V |
| I _R | reverse current | V _R = 200 V; T _j = 25 °C | - | | 6 | 30 | μA |
| | | V _R = 200 V; T _j = 100 °C | - | | 0.2 | 0.6 | mA |
| Dynamic | characteristics | | I | | | | |
| Qr | recovered charge | $I_{\text{F}} = 2 \text{ A}; \text{V}_{\text{R}} = 30 \text{V}; \text{d}_{\text{F}}/\text{d}\text{t} = 20 \text{A}/\mu\text{s}; \\ \text{T}_{\text{j}} = 25 ^{\circ}\text{C}$ | - | | 8 | 12.5 | nC |
| t _{rr} | reverse recovery time | $I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 100 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; \text{ ramp recovery}; Fig. 5$ | - | | 20 | 25 | ns |
| | | $I_F = 0.5 \text{ A to } I_R = 1 \text{ A}; T_j = 25 \text{ °C};$ measured at $I_R = 0.25 \text{ A};$ step recovery; Fig. 6 | - | | 10 | 20 | ns |
| V _{FR} | forward recovery voltage | I _F = 1 A; dI _F /dt = 10 A/μs; T _j = 25 °C; <u>Fig. 7</u> | - | | - | 1 | V |

Dual ultrafast power diode

BYV32EB-200



11. Package outline



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Product data sheet

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Dual ultrafast power diode

12. Legal information

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| Document status [1][2] | Product status [3] | Definition |
|--------------------------------------|-----------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification | This document contains data from the preliminary specification. |
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